

# IEEE TRANSACTIONS ON ELECTRON DEVICES

A PUBLICATION OF THE IEEE ELECTRON DEVICES SOCIETY



FEBRUARY 2014

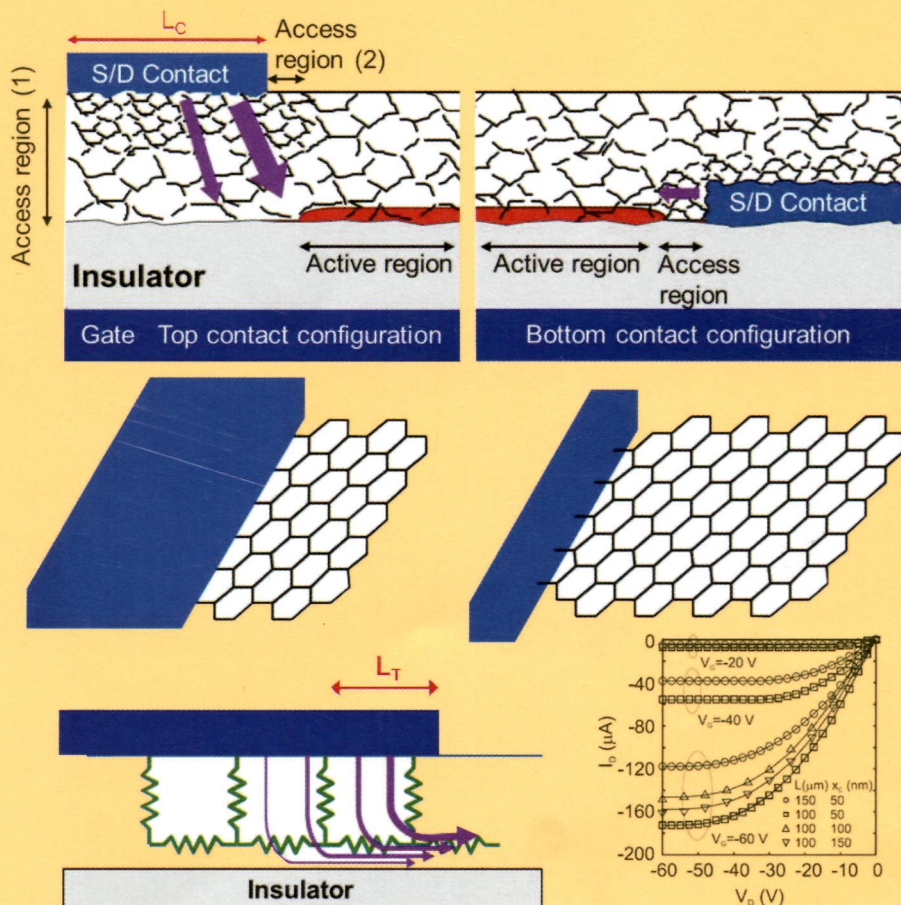
VOLUME 61

NUMBER 2

IETDAI

(ISSN 0018-9383)

SPECIAL ISSUE ON COMPACT MODELING OF EMERGING DEVICES



Configurations, contact effects and modeling of organic transistors.

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## SPECIAL ISSUE ON COMPACT MODELING OF EMERGING DEVICES

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